**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Extended temperature range T<sub>i</sub> = 175 °C
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1000 V HBM (class H1C)
- · AEC-Q101 qualified

### 3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Max  | Unit |  |
|-------------------|----------------------------------|--|-----|-----|-----|------|------|--|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | -20  | V    |  |
| $V_{GS}$          | gate-source voltage              |  |     | -12 | -   | 12   | V    |  |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C                   | [1] | -   | -   | -4.7 | Α    |  |
| Static characte   | Static characteristics           |  |     |     |     |      |      |  |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -4.7 \text{ A}; T_j = 25 \text{ °C}$ |     | -   | 43  | 50   | mΩ   |  |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline    | Graphic symbol |
|-----|--------|-------------|-----------------------|----------------|
| 1   | D      | drain       | <u> </u>              | D<br>-         |
| 2   | D      | drain       |                       |                |
| 3   | G      | gate        | 0<br>                 | g <b>∠</b>     |
| 4   | S      | source      | SC-74; TSOP6 (SOT457) | │              |
| 5   | D      | drain       |                       |                |
| 6   | D      | drain       |                       | s              |
|     |        |             |                       | 017aaa259      |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package      |  |         |  |  |
|-------------|--------------|--|---------|--|--|
|             | Name         | Description  | Version |  |  |
| PMN40XPEA   | SC-74; TSOP6 | plastic, surface-mounted package (SC-74; TSOP6); 6 leads | SOT457  |  |  |

# 7. Marking

### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMN40XPEA   | 6F           |

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter  | Conditions  |     | Min | Max  | Unit |
|----------------------|--|---|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                             | T <sub>j</sub> = 25 °C  |     | -   | -20  | V    |
| $V_{GS}$             | gate-source voltage                              |   |     | -12 | 12   | V    |
| I <sub>D</sub>       | drain current                                    | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C                  | [1] | -   | -4.7 | А    |
|                      |  | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C                 | [1] | -   | -3   | А    |
| I <sub>DM</sub>      | peak drain current                               | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                 |     | -   | -19  | Α    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>amb</sub> = 25 °C  | [2] | -   | 660  | mW   |
|                      |  |   | [1] | -   | 1.7  | W    |
|                      |  | T <sub>sp</sub> = 25 °C   |     | -   | 7.5  | W    |
| Tj                   | junction temperature                             |   |     | -55 | 175  | °C   |
| T <sub>amb</sub>     | ambient temperature                              |   |     | -55 | 175  | °C   |
| T <sub>stg</sub>     | storage temperature                              |   |     | -65 | 175  | °C   |
| Source-drain o       | diode  |   |     |     | •    |      |
| Is                   | source current                                   | T <sub>amb</sub> = 25 °C  | [1] | -   | -1.7 | Α    |
| ESD maximum          | n rating   |   |     | '   | •    |      |
| V <sub>ESD</sub>     | electrostatic discharge voltage                  | НВМ   | [3] | -   | 1000 | V    |
| Avalanche rug        | gedness  |   |     | 1   |      | ,    |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | $T_{j(init)}$ = 25 °C; $I_D$ = -1.5 A; DUT in avalanche (unclamped) |     | -   | 15   | mJ   |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain  $^2$ .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

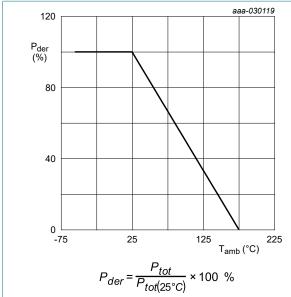


Fig. 1. Normalized total power dissipation as a function of ambient temperature

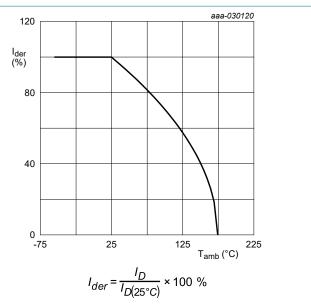


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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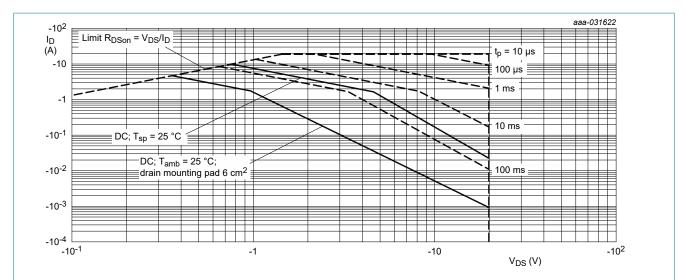


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

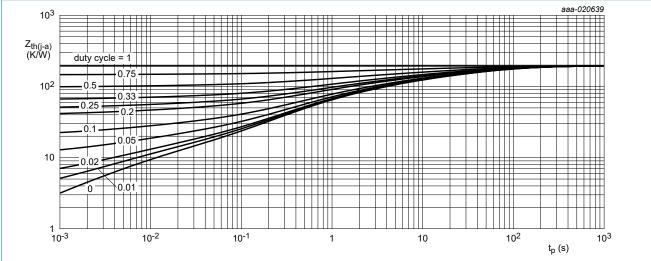
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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

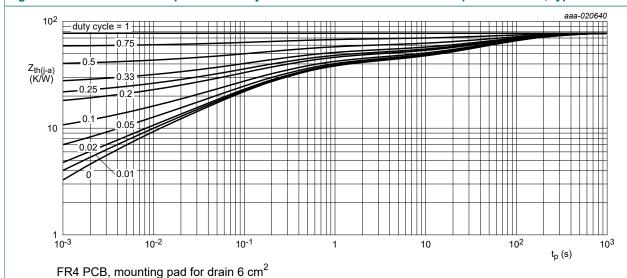
| Symbol              | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|---------------------|--|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$       | thermal resistance from                          | in free air | [1] | -   | 195 | 225 | K/W  |
| junction to ambient | junction to ambient                              |             | [2] | -   | 78  | 90  | K/W  |
| $R_{th(j-sp)}$      | thermal resistance from junction to solder point |             |     | -   | 15  | 20  | K/W  |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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## 10. Characteristics

#### **Table 7. Characteristics**

| Symbol   | Parameter  | Conditions   | Min  | Тур   | Max  | Unit |
|--|--|--|------|-------|------|------|
| Static chara                                       | acteristics  |  |      |       |      |      |
| V <sub>(BR)DSS</sub>                               | drain-source<br>breakdown voltage  | $I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C                              | -20  | -     | -    | V    |
| $V_{GSth}$   | gate-source threshold voltage  | $I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                        | -0.6 | -0.95 | -1.3 | V    |
| I <sub>DSS</sub>                                   | drain leakage current  | $V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$              | -    | -     | -1   | μΑ   |
| I <sub>GSS</sub>                                   | gate leakage current   | V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C           | -    | -     | -10  | μΑ   |
|  |  | V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C            | -    | -     | 10   | μΑ   |
|  |  | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$       | -    | -     | -2   | μΑ   |
|  |  | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C           | -    | -     | 2    | μΑ   |
| R <sub>DSon</sub> drain-source on-state resistance |  | $V_{GS} = -8 \text{ V}; I_D = -4.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$         | -    | 39    | 46   | mΩ   |
|  | resistance   | V <sub>GS</sub> = -8 V; I <sub>D</sub> = -4.7 A; T <sub>j</sub> = 175 °C         | -    | 59    | 70   | mΩ   |
|  |  | $V_{GS} = -4.5 \text{ V}; I_D = -4.7 \text{ A}; T_j = 25 \text{ °C}$             | -    | 43    | 50   | mΩ   |
|  | $V_{GS} = -2.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | -  | 64   | 78    | mΩ   |      |
| 9 <sub>fs</sub>                                    | forward transconductance   | $V_{DS} = -10 \text{ V}; I_D = -4.7 \text{ A}; T_j = 25 \text{ °C}$              | -    | 9.5   | -    | S    |
| R <sub>G</sub>                                     | gate resistance  | f = 1 MHz  | -    | 21    | -    | Ω    |
| Dynamic ch   | naracteristics   |  |      | '     |      |      |
| Q <sub>G(tot)</sub>                                | total gate charge  | V <sub>DS</sub> = -10 V; I <sub>D</sub> = -5.8 A; V <sub>GS</sub> = -4.5 V;      | -    | 10.6  | 16   | nC   |
| Q <sub>GS</sub>                                    | gate-source charge   | T <sub>j</sub> = 25 °C   | -    | 2.1   | -    | nC   |
| Q <sub>GD</sub>                                    | gate-drain charge  | 1  | -    | 3.6   | -    | nC   |
| C <sub>iss</sub>                                   | input capacitance  | V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                       | -    | 1025  | -    | pF   |
| C <sub>oss</sub>                                   | output capacitance   | T <sub>j</sub> = 25 °C   | -    | 137   | -    | pF   |
| C <sub>rss</sub>                                   | reverse transfer capacitance   |  | -    | 113   | -    | pF   |
| t <sub>d(on)</sub>                                 | turn-on delay time   | $V_{DS}$ = -10 V; $I_D$ = -5.8 A; $V_{GS}$ = -4.5 V;                             | -    | 6     | -    | ns   |
| t <sub>r</sub>                                     | rise time  | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$   | -    | 17    | -    | ns   |
| t <sub>d(off)</sub>                                | turn-off delay time  |  | -    | 23    | -    | ns   |
| t <sub>f</sub>                                     | fall time  | 1  | -    | 19    | -    | ns   |
| Source-dra   | in diode   |  | 1    |       |      |      |
| V <sub>SD</sub>                                    | source-drain voltage   | I <sub>S</sub> = -1.7 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C           | -    | -0.8  | -1.2 | V    |
| t <sub>rr</sub>                                    | reverse recovery time  | $I_S = -2 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | -    | 17    | -    | ns   |
| Qr   | recovered charge   | V <sub>DS</sub> = -10 V; T <sub>j</sub> = 25 °C                                  | -    | 5     | -    | nC   |

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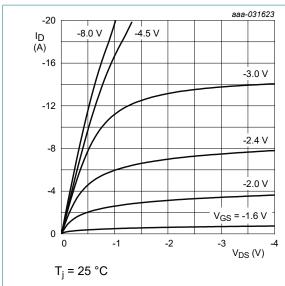


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

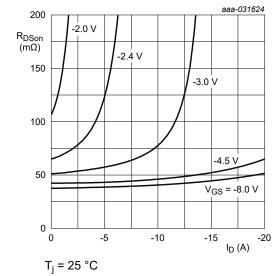


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

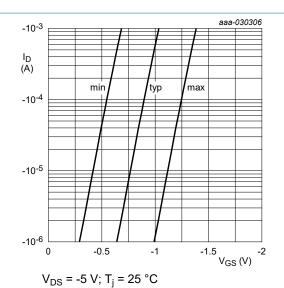


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

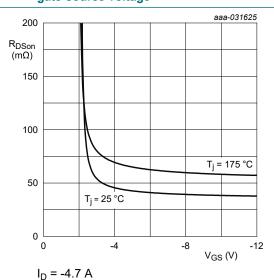


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 20 V, P-channel Trench MOSFET

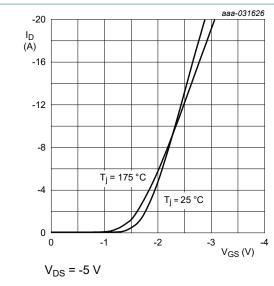


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

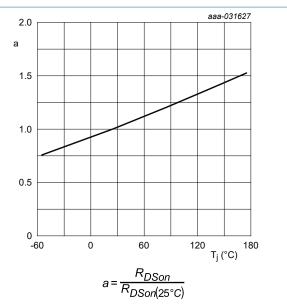


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

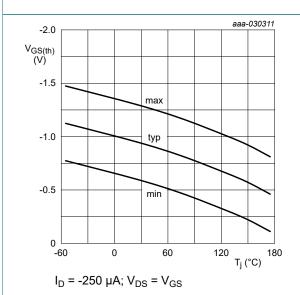


Fig. 12. Gate-source threshold voltage as a function of junction temperature

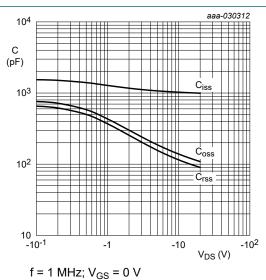


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 20 V, P-channel Trench MOSFET

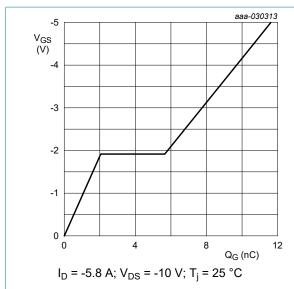


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

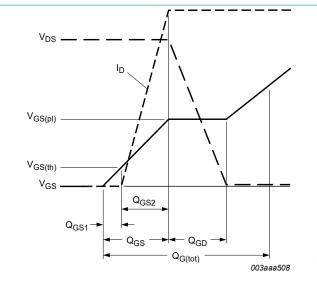


Fig. 15. Gate charge waveform definitions

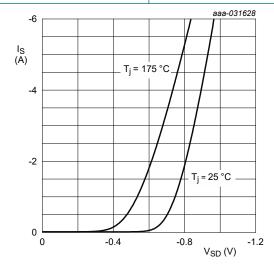
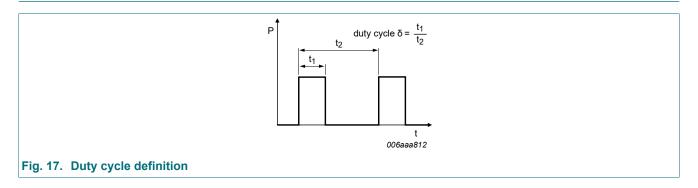


Fig. 16. Source current as a function of source-drain voltage; typical values

20 V, P-channel Trench MOSFET

## 11. Test information



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 20 V, P-channel Trench MOSFET

# 12. Package outline

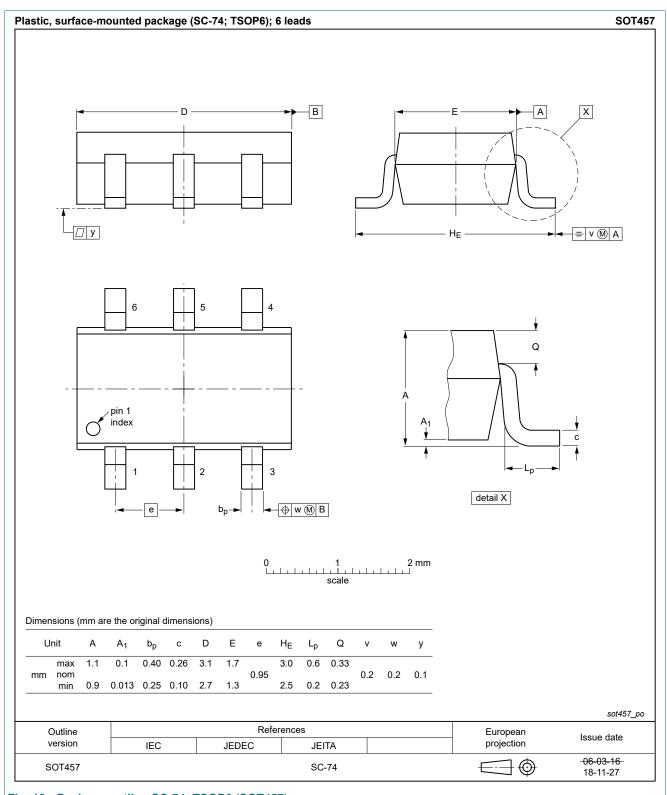
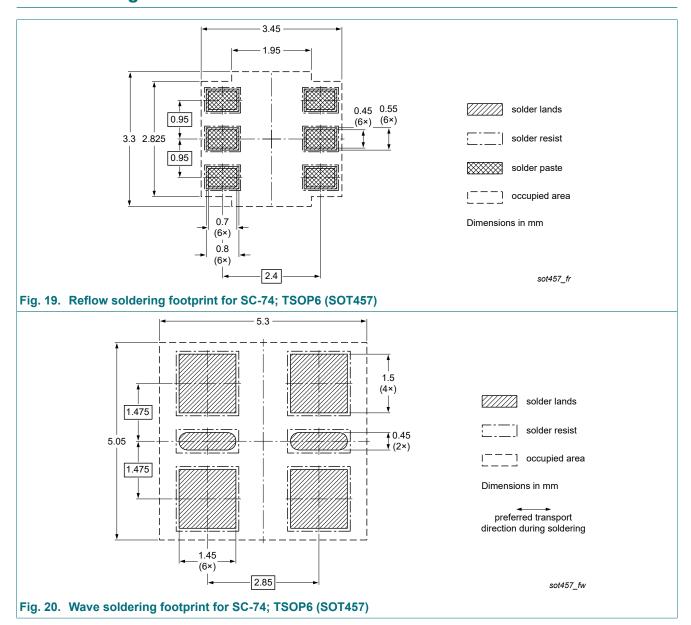


Fig. 18. Package outline SC-74; TSOP6 (SOT457)

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## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMN40XPEA v.1 | 20200707     | Product data sheet | -             | -          |

### 20 V, P-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
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| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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